

TIP35A, TIP35B, TIP35C (NPN); TIP36A, TIP36B, TIP36C (PNP)

TIP35B, TIP35C, TIP36B, and TIP36C are Preferred Devices

Complementary Silicon High-Power Transistors

Designed for general-purpose power amplifier and switching applications.

Features

- 25 A Collector Current
- Low Leakage Current –
 $I_{CEO} = 1.0 \text{ mA @ } 30 \text{ and } 60 \text{ V}$
- Excellent DC Gain –
 $h_{FE} = 40 \text{ Typ @ } 15 \text{ A}$
- High Current Gain Bandwidth Product –
 $|h_{fe}| = 3.0 \text{ min @ } I_C = 1.0 \text{ A, } f = 1.0 \text{ MHz}$
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	TIP35A TIP36A	TIP35B TIP36B	TIP35C TIP36C	Unit
Collector – Emitter Voltage	V_{CEO}	60	80	100	Vdc
Collector – Base Voltage	V_{CB}	60	80	100	Vdc
Emitter – Base Voltage	V_{EB}	5.0			Vdc
Collector Current – Continuous – Peak (Note 1)	I_C	25 40			A dc
Base Current – Continuous	I_B	5.0			A dc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	125			W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150			$^\circ\text{C}$
Unclamped Inductive Load	E_{SB}	90			mJ

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^\circ\text{C/W}$
Junction-to-Free-Air Thermal Resistance	$R_{\theta JA}$	35.7	$^\circ\text{C/W}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

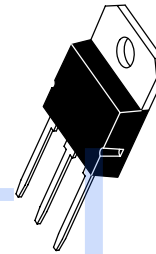
1. Pulse Test: Pulse Width = 10 ms, Duty Cycle $\leq 10\%$.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

25 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60–100 VOLTS, 125 WATTS



SOT-93 (TO-218)
CASE 340D
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
TIP3xx = Device Code
xx = 5A, 5B, 5C
6A, 6B, 6C
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

TIP35A, TIP35B, TIP35C (NPN); TIP36A, TIP36B, TIP36C (PNP)

ORDERING INFORMATION

Device	Package	Shipping
TIP35A	SOT-93 (TO-218)	30 Units / Rail
TIP35AG	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP35B	SOT-93 (TO-218)	30 Units / Rail
TIP35BG	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP35C	SOT-93 (TO-218)	30 Units / Rail
TIP35CG	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP36A	SOT-93 (TO-218)	30 Units / Rail
TIP36AG	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP36B	SOT-93 (TO-218)	30 Units / Rail
TIP36BG	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail
TIP36C	SOT-93 (TO-218)	30 Units / Rail
TIP36CG	SOT-93 (TO-218) (Pb-Free)	30 Units / Rail

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 2) (I _C = 30 mA, I _B = 0)	TIP35A, TIP36A TIP35B, TIP36B TIP35C, TIP36C	V _{CEO(sus)}	60 80 100	- - -	Vdc
Collector-Emitter Cutoff Current (V _{CE} = 30 V, I _B = 0) (V _{CE} = 60 V, I _B = 0)	TIP35A, TIP36A TIP35B, TIP35C, TIP36B, TIP36C	I _{CEO}	- -	1.0 1.0	mA
Collector-Emitter Cutoff Current (V _{CE} = Rated V _{CEO} , V _{EB} = 0)		I _{CES}	-	0.7	mA
Emitter-Base Cutoff Current (V _{EB} = 5.0 V, I _C = 0)		I _{EBO}	-	1.0	mA

ON CHARACTERISTICS (Note 2)

DC Current Gain (I _C = 1.5 A, V _{CE} = 4.0 V) (I _C = 15 A, V _{CE} = 4.0 V)		h _{FE}	25 15	- 75	-
Collector-Emitter Saturation Voltage (I _C = 15 A, I _B = 1.5 A) (I _C = 25 A, I _B = 5.0 A)		V _{CE(sat)}	- -	1.8 4.0	Vdc
Base-Emitter On Voltage (I _C = 15 A, V _{CE} = 4.0 V) (I _C = 25 A, V _{CE} = 4.0 V)		V _{BE(on)}	- -	2.0 4.0	Vdc

DYNAMIC CHARACTERISTICS

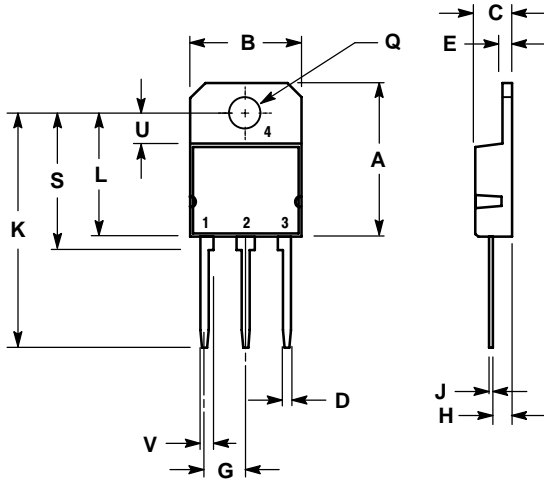
Small-Signal Current Gain (I _C = 1.0 A, V _{CE} = 10 V, f = 1.0 kHz)		h _{fe}	25	-	-
Current-Gain — Bandwidth Product (I _C = 1.0 A, V _{CE} = 10 V, f = 1.0 MHz)		f _T	3.0	-	MHz

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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PACKAGE DIMENSIONS

SOT-93 (TO-218)
CASE 340D-02
ISSUE E



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00 REF		1.220 REF	
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00 REF		0.157 REF	
V	1.75 REF		0.069	

- STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR